

CN810-40P

Infrared LED CHIP

<Specifications>

Commodity Type and Physical Characteristics	
Material	GaAlAs/GaAlAs(DDH)
Top Side P(anode)side	Au Alloy
Bottom Side N(cathode)side	Au Alloy
Electrode Pattern	Fig.1
Chip Size	Fig.2
Chip Thickness	Fig.2
Emission Area	Fig.2

Electro-Optical Characteristics [Ta=25°C]						
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	IF=20mA		1.40	1.60	V
Reverse Current	IR	VR=5V			10	uA
Power Intensity	PO	IF=20mA	3.0	5.0		mW
Peak Wavelength	λP	IF=20mA	800	810	820	nm
Spectral Radiation Bandwidth	$\Delta\lambda$	IF=20mA		40		nm
Rise Time	tr	IF=20mA		25		ns
Fall Time	tf	IF=20mA		15		ns

Die shall be mounted on TO-18 gold header without resin coated.

[Unit:um]

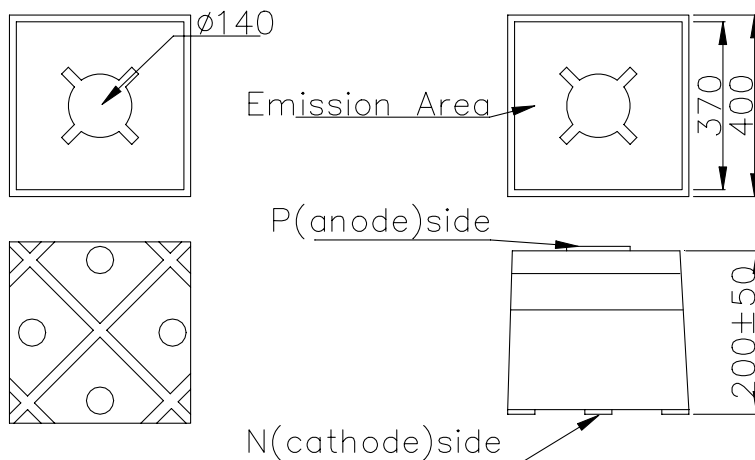


Fig.1 Electrode Pattern

Fig.2 Chip Size and Emission Area